Amendments to the Specification:

Please replace the paragraph starting on page 13 line 29 through page 14 line 24 with the following amended paragraph:

For the channel layer 17, a material having a composition similar to that of the first embodiment. However, in the second embodiment, one doped with relatively large amount of impurities can be used. For the substrate 16, similarly to the case of the first embodiment, a material having high compatibility is used properly according to the channel layer 17. For the buffer layer [[17]] 18, if group II oxide or group III nitride is used for the channel layer 17, then a slightly doped or undoped insulating material having the same composition as that of the channel layer 17 can be used. For example, if e.g., ZnO is used for the channel layer 17, for the buffer layer [[17]] 18, an insulating material such as insulating ZnO or the like slightly doped with an element capable of taking valence of 1 value or a group V element, or an insulating semiconductor such as undoped pure insulating ZnO or the like, can be used. As the element taking valence of 1 value, e.g., group I elements (Li, Na, K, Rb, and Cs), Cu, Ag, Au, and so on, are available. As the group V element, N, P, As, Sb, Bi, and so on, are available. In the second embodiment, as in the case described above with reference to the first embodiment, the combination of each materials for the channel layer 17, for the buffer layer 18 with the same materials in composition as the thin film material of the channel layer 17, and for the substrate 16 can be properly selected by considering the compatibility of the lattice constants.